



Schottky Barrier Diode

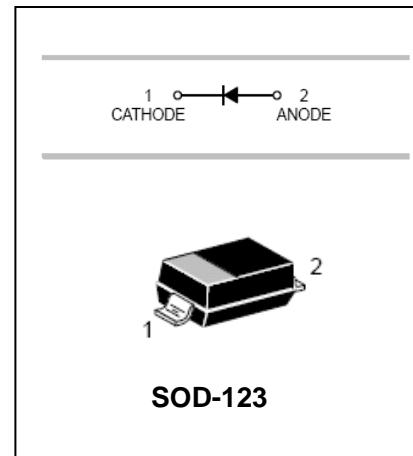
BAS40H

FEATURES

- Small and flat lead SMD plastic package.
- Flat leades:excellent coplanarity and improved Thermal behavior.
- Low capacitance.
- High switching speed.
- Low leakage current.



Lead-free



APPLICATIONS

- Ultra high-speed switching.
- Voltage clamping.

ORDERING INFORMATION

Type No.	Marking	Package Code
BAS40H	AJ	SOD-123

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Limits	Unit
Forward Voltage@ $I_F=10\text{mA}$	V_F	500	mV
Reverse Voltage	V_R	40	V
Forward Current	I_F	120	mA
Repetitive Peak Forward Current	I_{FRM}	120	mA
Non-repetitive Peak Forward Current	I_{FSM}	200	mA
Power Dissipation	P_d	375	mW
Storage and ambient temperature range	T_{amb}, T_{stg}	-65 to +150	°C
Junction temperature	T_j	150	°C



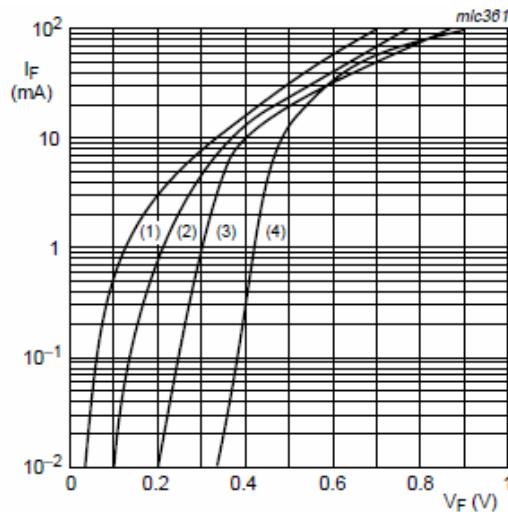
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ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ C$ unless otherwise specified

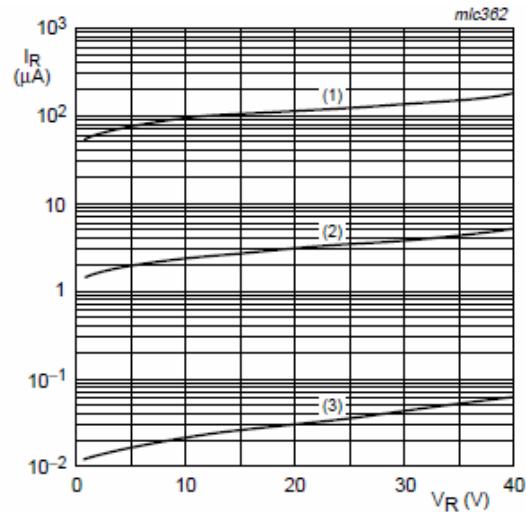
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R=10\mu A$	40			V
Forward Voltage	V_F	$I_F=1mA$			0.38	V
	V_F	$I_F=40mA$			1.00	V
Reverse Current	I_R	$V_R=30V$			1	μA
		$V_R=40V$			10	μA
Diode Capacitance	C_d	$V_R=0V, f=1MHz$			5	pF

TYPICAL CHARACTERISTICS @ $T_a=25^\circ C$ unless otherwise specified



- (1) $T_{amb} = 125^\circ C$
- (2) $T_{amb} = 85^\circ C$
- (3) $T_{amb} = 25^\circ C$
- (4) $T_{amb} = -40^\circ C$

Fig 1. Forward current as a function of forward Temperature



- (1) $T_{amb} = 125^\circ C$
- (2) $T_{amb} = 85^\circ C$
- (3) $T_{amb} = 25^\circ C$

Fig 2. Reverse current as a function of junction voltage; typical values



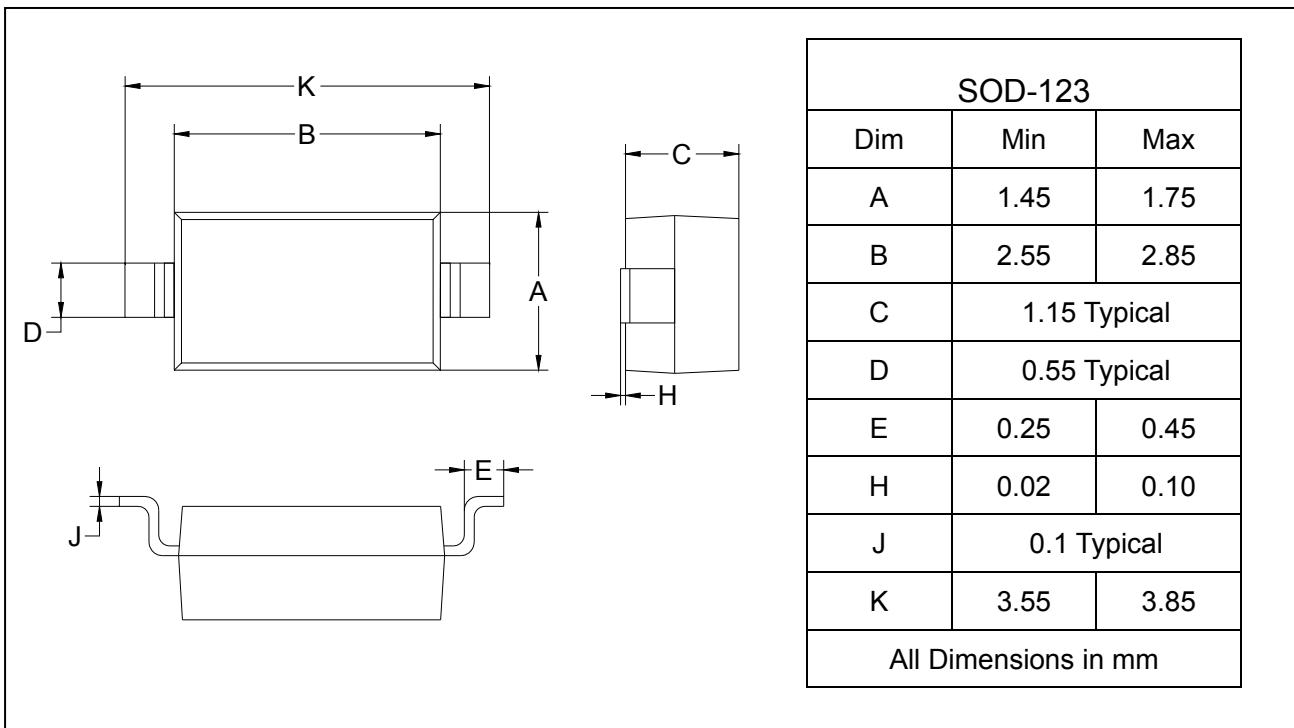
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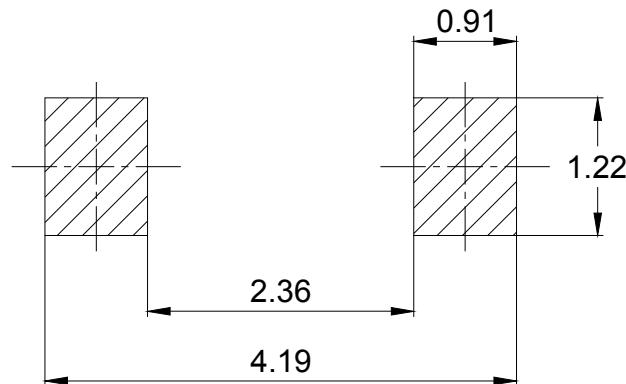
PACKAGE OUTLINE

Plastic surface mounted package

SOD-123



SOLDERING FOOTPRINT



Unit: mm

PACKAGE INFORMATION

Device	Package	Shipping
BAS40H	SOD-123	3000/Tape&Reel